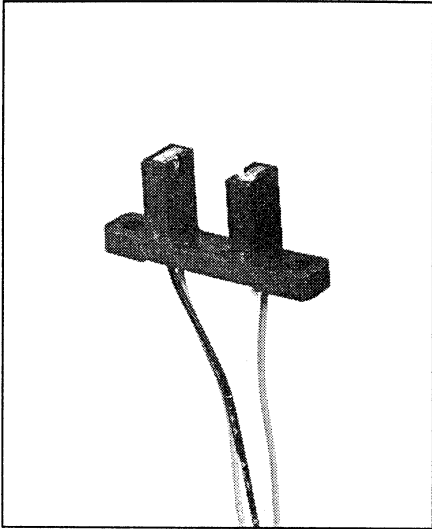


Deep Gap Slotted Optical Switch Type OPB815W

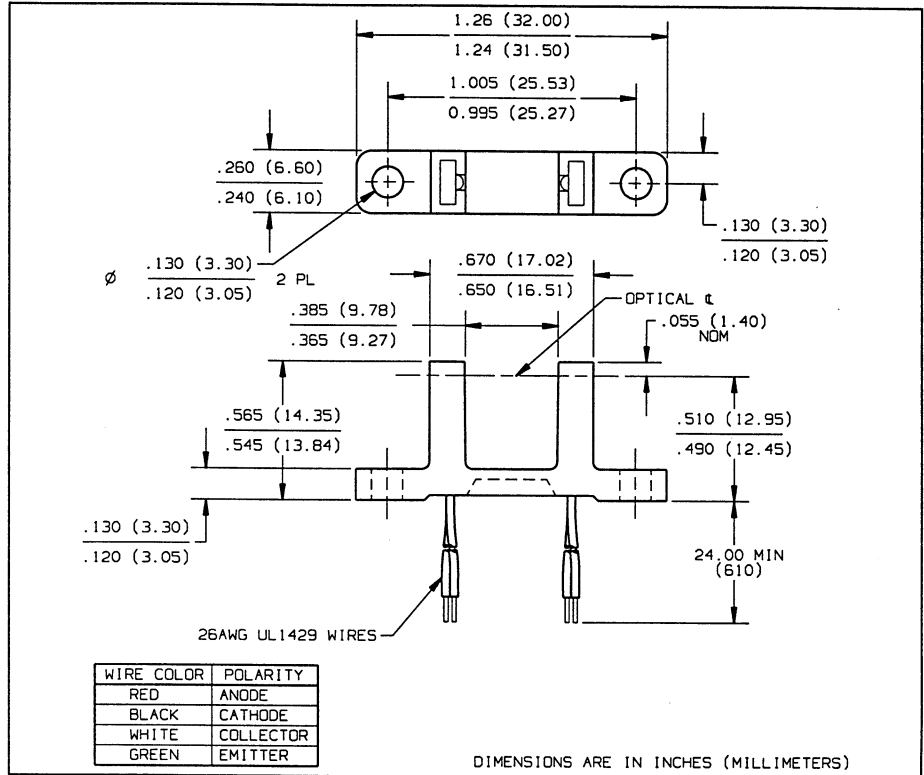


Features

- Non-contact switching
- 24" minimum, 26 AWG wire leads
- 0.375" (9.53 mm) wide slot
- 0.430" (10.92 mm) deep slot

Description

The OPB815W consists of an infrared emitting diode and an NPN silicon phototransistor mounted in a low cost plastic housing on opposite sides of a 0.375" (9.53 mm) wide, 0.430" (10.9 mm) deep slot. Phototransistor switching takes place whenever an opaque object passes through the slot. Available with PC board mountable leads as OPB815L.



Absolute Maximum Ratings ($T_A = 25^\circ\text{C}$ unless otherwise noted)

Storage and Operating Temperature -40°C to $+80^\circ\text{C}$
Lead Soldering Temperature [1/16 inch (1.6 mm) from case for 5 sec. with soldering iron] $240^\circ\text{C}^{(1)}$

Input Diode

Continuous Forward Current 50 mA
Peak Forward Current (1 μs pulse width, 300 pps) 3.0 A
Reverse Voltage 2.0 V
Power Dissipation $100\text{ mW}^{(2)}$

Output Phototransistor

Collector-Emitter Voltage 30 V
Emitter-Collector Voltage 5.0 V
Power Dissipation $100\text{ mW}^{(2)}$

Notes:

- (1) RMA flux is recommended. Duration can be extended to 10 sec. max when flow soldering.
- (2) Derate linearly $1.67\text{ mW}/^\circ\text{C}$ above 25°C .
- (3) Methanol or isopropanol are recommended as cleaning agents. Plastic housing is soluble in chlorinated hydrocarbons and ketones.
- (4) All parameters tested using pulse technique.

Type OPB815W

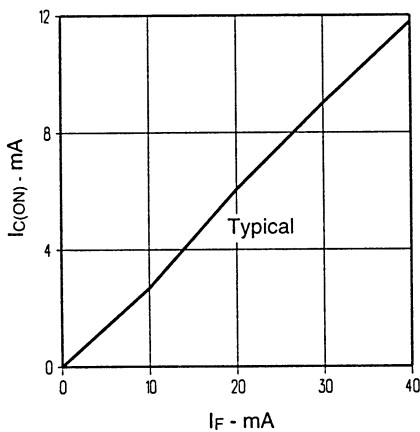
Electrical Characteristics ($T_A = 25^\circ\text{C}$ unless otherwise noted)

| SYMBOL | PARAMETER | MIN | MAX | UNITS | TEST CONDITIONS |
|-------------------------------|--------------------------------------|-----|------|---------------|--|
| Input Diode | | | | | |
| V_F | Forward Voltage | | 1.70 | V | $I_F = 20\text{ mA}$ |
| I_R | Reverse Current | | 100 | μA | $V_R = 2.0\text{ V}$ |
| Output Phototransistor | | | | | |
| $V_{(BR)CEO}$ | Collector-Emitter Breakdown Voltage | 30 | | V | $I_C = 1.00\text{ mA}$ |
| $V_{(BR)ECO}$ | Emitter-Collector Breakdown Voltage | 5.0 | | V | $I_E = 100\ \mu\text{A}$ |
| I_{CEO} | Collector-Emitter Dark Current | | 100 | nA | $V_{CE} = 10.0\text{ V}, I_F = 0, E_e = 0$ |
| Coupled | | | | | |
| $V_{CE(SAT)}$ | Collector-Emitter Saturation Voltage | | 0.40 | V | $I_C = 500\ \mu\text{A}, I_F = 20\text{ mA}$ |
| $I_{C(ON)}$ | On-State Collector Current | 1 | | mA | $V_{CE} = 10.0\text{ V}, I_F = 20\text{ mA}$ |

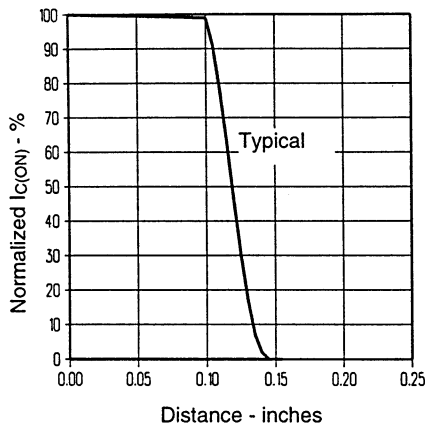
SLOTTED OPTICAL SWITCHES

Typical Performance Curves

Collector Current vs LED Drive



Normalized $I_{C(ON)}$ vs Distance (X Axis Blocked)



Normalized $I_{C(ON)}$ vs Distance (Y Axis Blocked)

